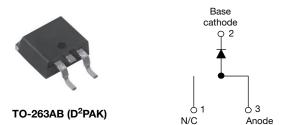
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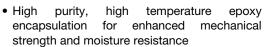
High Performance Schottky Rectifier, 10 A



PRODUCT SUMMARY						
Package	TO-263AB (D ² PAK) 10 A 35 V, 45 V 0.57 V 15 mA at 125 °C 150 °C Single die 8.0 mJ					
I _{F(AV)}	10 A					
V _R	35 V, 45 V					
V _F at I _F	0.57 V					
I _{RM} max.	15 mA at 125 °C					
T _J max.	150 °C					
Diode variation	Single die					
E _{AS}	8.0 mJ					

FEATURES

- 150 °C T_J operation
- TO-220 and D2PAK packages
- Low forward voltage drop
- High frequency operation





ROHS COMPLIANT HALOGEN FREE

- Guard ring for enhanced ruggedness and long term reliability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201, class 1A whisker test
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

DESCRIPTION

This Schottky rectifier has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 150 °C junction temperature. Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS								
SYMBOL	UNITS							
I _{F(AV)}	Rectangular waveform	10	۸					
I _{FRM}	T _C = 135 °C	20	A					
V _{RRM}		35, 45	V					
I _{FSM}	t _p = 5 μs sine	1060	Α					
V _F	10 A _{pk} , T _J = 125 °C	0.57	V					
T _J	Range	-65 to +150	°C					

VOLTAGE RATINGS									
PARAMETER	SYMBOL	VS-MBRB1035PbF	VS-MBRB1045PbF	UNITS					
Maximum DC reverse voltage	V_R	35	45	V					
Maximum working peak reverse voltage	V_{RWM}	33	45	V					

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CON	VALUES	UNITS				
Maximum average forward current	I _{F(AV)}	T _C = 135 °C, rated V _R		10				
Peak repetitive forward current	I _{FRM}	Rated V _R , square wave, 20 kHz, T	_C = 135 °C	20				
Non-repetitive surge current	I _{FSM}	Following any rated load condition and with rated V _{RRM} applied		1060	А			
		Surge applied at rated load condit	150					
Non-repetitive avalanche energy	E _{AS}	$T_J = 25$ °C, $I_{AS} = 2$ A, $L = 4$ mH	8	mJ				
Repetitive avalanche current	I _{AR}	Current decaying linearly to zero in Frequency limited by T _J maximum	2	Α				



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ELECTRICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CO	VALUES	UNITS				
		20 A	T _J = 25 °C	0.84				
Maximum forward voltage drop	V _{FM} (1)	10 A	T 105 °C	0.57	V			
		20 A	- T _J = 125 °C	0.72				
Maximum instantaneous reverse	1 (1)	T _J = 25 °C	Dated DC valtage	0.1	mA			
current	I _{RM} (1)	T _J = 125 °C	Rated DC voltage	15				
Threshold voltage	V _{F(TO)}	T - T movimum		0.354	V			
Forward slope resistance	r _t	rj = rj maximum	$T_J = T_J$ maximum		mΩ			
Maximum junction capacitance	C _T	V _R = 5 V _{DC} (test signal rang	600	pF				
Typical series inductance	L _S	Measured from top of term	8.0	nH				
Maximum voltage rate of change	dV/dt	Rated V _R	10 000	V/µs				

Note

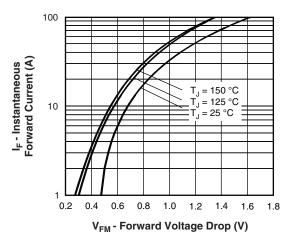
 $^{(1)}$ Pulse width < 300 μ s, duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	PARAMETER		TEST CONDITIONS	VALUES	UNITS		
Maximum junction tempera	ture range	TJ		-65 to +150	°C		
Maximum storage tempera	ture range	T _{Stg}		-65 to +175	C		
Maximum thermal resistant junction to case	e,	R _{thJC}	DC operation	2.0			
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased (Only for TO-220)	0.50	°C/W		
Approximate weight				2	g		
Approximate weight				0.07	oz.		
Maunting toward	minimum			6 (5)	kgf · cm		
Mounting torque maximur				12 (10)	(lbf · in)		
Marking device			Occupation D2DAY		31035		
			Case style D ² PAK	MBRE	31045		

= 150

100

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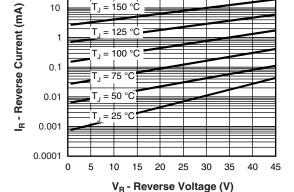


Fig. 1 - Maximum Forward Voltage Drop Characteristics

Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

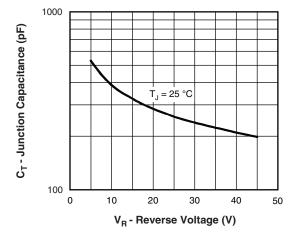


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

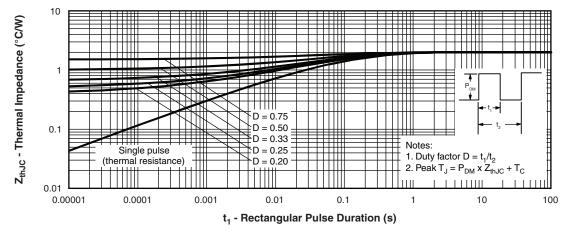


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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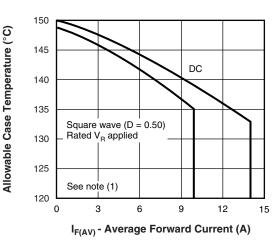


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

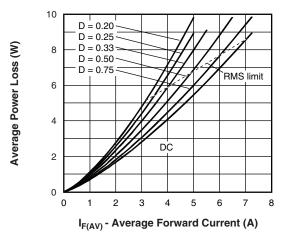


Fig. 6 - Forward Power Loss Characteristics

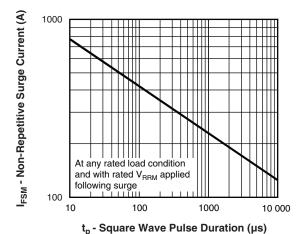


Fig. 7 - Maximum Non-Repetitive Surge Current

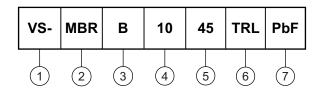
Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \ x \ R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \ x \ V_{FM} \ \text{at } (I_{F(AV)}/D) \ \text{(see fig. 6)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \ x \ I_R \ (1 - D); \ I_R \ \text{at } V_{R1} = \text{rated } V_R \\ \end{array}$

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

Essential part number

3 - B = surface mount

Current rating (10 = 10 A)

- Voltage ratings 35 = 35 V 45 = 45 V

• None = tube (50 pieces)

• TRL = tape and reel (left oriented)

• TRR = tape and reel (right oriented)

7 - PbF = lead (Pb)-free

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95046						
Part marking information	www.vishay.com/doc?95054					
Packaging information	www.vishay.com/doc?95032					
SPICE model	www.vishay.com/doc?95293					



Vishay Semiconductors

D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		inches		NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



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Vishay

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PMAD1108-LF RB160M-50TR RB520S-30 RB551V-30 DD350N18K DZ435N40K DZ600N16K BAS16E6433HTMA1 BAS 3010S02LRH E6327 BAT 54-02LRH E6327 IDL02G65C5XUMA1 NSR05F40QNXT5G JANS1N6640 SB07-03C-TB-H SB1003M3-TL-W
SBAT54CWT1G SBM30-03-TR-E SK32A-LTP SK33A-TP SK34A-TP SK34B-TP SMD1200PL-TP ACDBN160-HF SS3003CH-TL-E
STPS30S45CW PDS3100Q-7 GA01SHT18 CRS10I30A(TE85L,QM MBR1240MFST1G MBRB30H30CT-1G BAS28E6433HTMA1 BAS
70-02L E6327 HSB123JTR-E JANTX1N5712-1 VS-STPS40L45CW-N3 DD350N12K SB007-03C-TB-E SB10015M-TL-E SB1003M3-TL-E SK110-LTP SK154-TP SK32A-TP SK33B-TP